# Advance Information

# **Silicon Controlled Rectifiers**

# **Reverse Blocking Thyristors**

Designed for high volume, low cost, industrial and consumer applications such as motor control, process control, temperature, light and speed control.

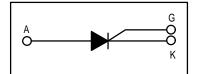
- Small Size
- · Passivated Die for Reliability and Uniformity
- Low Level Triggering and Holding Characteristics
- Available in Surface Mount Lead Form Case 369A

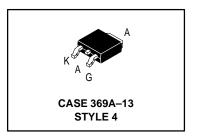
### ORDERING INFORMATION

To Obtain "DPAK" in Surface Mount Leadform (Case 369A):
 Shipped in 16 mm Tape and Reel — Add "T4" Suffix to Device Number,
 i.e., MCR718T4

# MCR716 MCR718

SCRs 4.0 AMPERES RMS 400 thru 600 VOLTS





### MAXIMUM RATINGS (T<sub>.J</sub> = 25°C unless otherwise noted.)

| Characteristic  |                  | Symbol               | Value       | Unit               |
|---|------------------|----------------------|-------------|--------------------|
| Peak Repetitive Off–State Voltage <sup>1</sup><br>Peak Repetitive Reverse Voltage<br>$(T_J = -40 \text{ to } +110^{\circ}\text{C}, R_{GK} = 1 \text{ K}\Omega)$ | MCR716<br>MCR718 | VDRM<br>VRRM         | 400<br>600  | Volts              |
| On-State RMS Current<br>(All conduction Angles; T <sub>C</sub> = 90°C)  |                  | I <sub>T</sub> (RMS) | 4.0         | Amps               |
| Average On-State Current (All conduction Angles; T <sub>C</sub> = 90°C)   |                  | lT(AV)               | 2.6         | Amps               |
| Peak Non–Repetitive Surge Current<br>(One Half Cycle, 60 Hz, T <sub>J</sub> = 110°C)  |                  | ITSM                 | 25          | Amps               |
| Circuit Fusing Consideration (t = 8.3 msec)   |                  | l <sup>2</sup> t     | 2.6         | A <sup>2</sup> sec |
| Peak Gate Power (Pulse Width ≤ 10 µs, T <sub>C</sub> = 90°C)  |                  | P <sub>GM</sub>      | 0.5         | Watt               |
| Average Gate Power (t = 8.3 msec, T <sub>C</sub> = 90°C)  |                  | P <sub>G(AV)</sub>   | 0.1         | Watt               |
| Peak Gate Current (Pulse Width $\leq$ 10 $\mu$ s, T <sub>C</sub> = 90°C)  |                  | I <sub>GM</sub>      | 0.2         | Amp                |
| Operating Junction Temperature Range  |                  | TJ                   | -40 to +110 | °C                 |
| Storage Temperature Range   |                  | T <sub>stg</sub>     | -40 to +150 | °C                 |

# THERMAL CHARACTERISTICS

| Characteristic   | Symbol         | Max | Unit |
|--|----------------|-----|------|
| Thermal Resistance, Junction to Case                   | $R_{	heta JC}$ | 3.0 | °C/W |
| Thermal Resistance, Junction to Ambient (Case 369A)(2) | $R_{	heta JA}$ | 80  | °C/W |

<sup>1..</sup>V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

2. Case 369A, when surface mounted on minimum recommended pad size.



# **MCR716 MCR718**

# **ELECTRICAL CHARACTERISTICS** (T $_{C}$ = 25°C and R $_{GK}$ = 1 K $\Omega$ unless otherwise noted.)

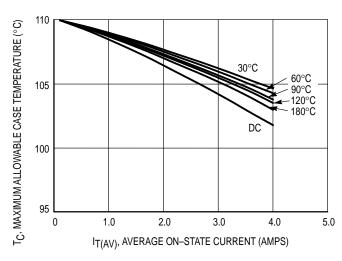
| Characteristic  | Symbol           | Min             | Тур            | Max           | Unit  |
|---|------------------|-----------------|----------------|---------------|-------|
| Peak Reverse Gate Blocking Voltage (IGR = 10 µA)  | VGRM             | 10              | 12.5           | 18            | Volts |
| Peak Forward Blocking Current <sup>1</sup> Peak Reverse Blocking Current <sup>3</sup> (VAK = Rated VDRM or VRRM)  T <sub>C</sub> = 25°C   | IDRM<br>IRRM     | _               | _              | 10            | μΑ    |
| $T_{C} = 110^{\circ}C$  |                  |                 |                | 200           |       |
| Peak Reverse Gate Blocking Current<br>(V <sub>GR</sub> = 10 V)  | <sup>I</sup> RGM | _               | _              | 1.2           | μΑ    |
| Peak On–State Voltage <sup>2</sup> (I <sub>TM</sub> = 5.0 A Peak) (I <sub>TM</sub> = 8.2 A Peak)  | V <sub>TM</sub>  | _               | 1.3<br>1.5     | 1.5<br>2.2    | Volts |
| Gate Trigger Current (Continuous dc) <sup>3</sup> $(V_D = 12 \text{ Vdc}, R_L = 30 \text{ Ohms}, T_C = 25^{\circ}\text{C})$ $(V_D = 12 \text{ Vdc}, R_L = 30 \text{ Ohms}, T_C = -40^{\circ}\text{C})$  | lGT              | 1.0             | 25<br>—        | 75<br>300     | μА    |
| Gate Trigger Voltage (Continuous dc) <sup>3</sup> $(V_D = 12 \text{ Vdc}, R_L = 30 \text{ Ohms}, T_C = 25^{\circ}\text{C})$ $(V_D = 12 \text{ Vdc}, R_L = 30 \text{ Ohms}, T_C = -40^{\circ}\text{C})$ $(V_D = 12 \text{ Vdc}, R_L = 30 \text{ Ohms}, T_C = 110^{\circ}\text{C})$ | VGT              | 0.3<br>—<br>0.2 | 0.55<br>—<br>— | 0.8<br>1<br>— | Volts |
| Holding Current <sup>1</sup> ( $V_D = 12 \text{ Vdc}$ , $I_G = 2.0 \text{ mA}$ , $I_{T(init)} = 200 \text{ mA}$ , $I_{C} = 25^{\circ}\text{C}$ ) ( $V_D = 12 \text{ Vdc}$ , $I_G = 2.0 \text{ mA}$ , $I_{T(init)} = 200 \text{ mA}$ , $I_{C} = -40^{\circ}\text{C}$ )             | Ιн               | 0.4             | 1.0<br>—       | 5.0<br>10     | mA    |
| Latching Current <sup>1</sup> ( $V_D = 12 \text{ Vdc}, I_G = 2.0 \text{ mA}, T_C = 25^{\circ}\text{C}$ ) ( $V_D = 12 \text{ Vdc}, I_G = 2.0 \text{ mA}, T_C = -40^{\circ}\text{C}$ )  | ΙL               | _<br>_          | _              | 5.0<br>10     | mA    |
| DYNAMIC CHARACTERISTICS   |                  | _               | -              | -             | -     |
| Total Turn-On Time  (Source Voltage = 12 V, Ro = 6 KO, Iz = 8 A(pk), Roy = 1 KO)  | tgt              | _               | 2.0            | 5.0           | μs    |

| Total Turn-On Time (Source Voltage = 12 V, R <sub>S</sub> = 6 K $\Omega$ , I <sub>T</sub> = 8 A(pk), R <sub>GK</sub> = 1 K $\Omega$ ) (V <sub>D</sub> = Rated V <sub>DRM</sub> , Rise Time = 20 ns, Pulse Width = 10 $\mu$ s) | <sup>t</sup> gt | _   | 2.0 | 5.0 | μѕ   |
|---|-----------------|-----|-----|-----|------|
| Critical Rate of Rise of Off–State Voltage (V <sub>D</sub> = 0.67 x Rated V <sub>DRM</sub> , Exponential Waveform, T <sub>J</sub> = 110°C)  | dv/dt           | 5.0 | 10  |     | V/μs |
| Repetitive Critical Rate of Rise of On–State Current (f = 60 Hz, $I_{PK}$ = 30 A, $PW$ = 100 $\mu$ s, $dIG/dt$ = 1 A/ $\mu$ s)  | di/dt           | _   | _   | 100 | A/μs |

<sup>1..</sup> Ratings apply for negative gate voltage or  $R_{GK}$  = 1 K $\Omega$ . Devices shall not have a positive gate voltage concurrently with a negative voltage on the anode. Devices should not be tested with a constant current source for forward and reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.

<sup>2...</sup>Pulse Test: Pulse Width  $\leq$  2 ms, Duty Cycle  $\leq$  2%.

<sup>3..</sup> Does not include  $R_{\mbox{GK}}$  current.





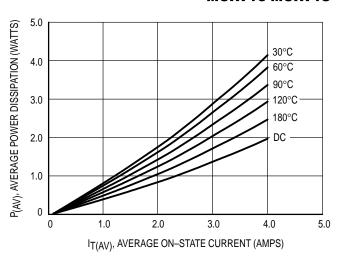


Figure 2. On-State Power Dissipation

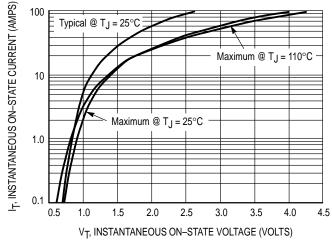
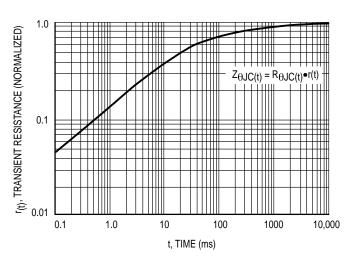


Figure 3. On-State Characteristics



**Figure 4. Transient Thermal Response** 

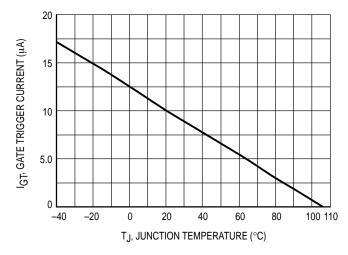


Figure 5. Typical Gate Trigger Current versus Junction Temperature

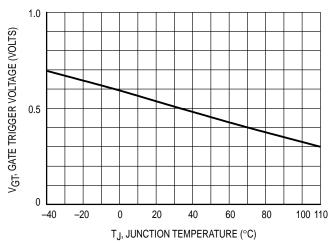
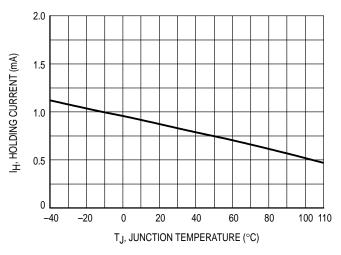


Figure 6. Typical Gate Trigger Voltage versus
Junction Temperature

#### **MCR716 MCR718**



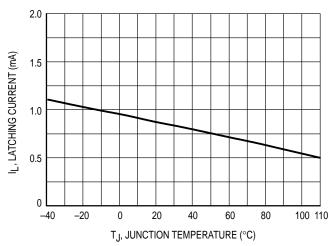
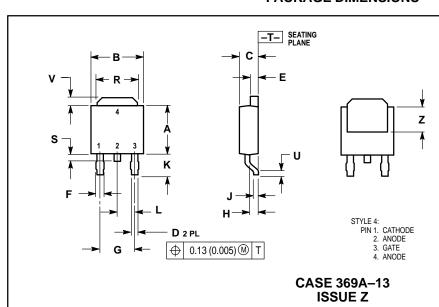


Figure 7. Typical Holding Current versus Junction Temperature

Figure 8. Typical Latching Current versus Junction Temperature

## PACKAGE DIMENSIONS



#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
  V14 5M 1082
- Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

|     | INCHES    |       | MILLIN   | IETERS |
|-----|-----------|-------|----------|--------|
| DIM | MIN       | MAX   | MIN      | MAX    |
| Α   | 0.235     | 0.250 | 5.97     | 6.35   |
| В   | 0.250     | 0.265 | 6.35     | 6.73   |
| С   | 0.086     | 0.094 | 2.19     | 2.38   |
| D   | 0.027     | 0.035 | 0.69     | 0.88   |
| Е   | 0.033     | 0.040 | 0.84     | 1.01   |
| F   | 0.037     | 0.047 | 0.94     | 1.19   |
| G   | 0.180     | BSC   | 4.58     | BSC    |
| Н   | 0.034     | 0.040 | 0.87     | 1.01   |
| J   | 0.018     | 0.023 | 0.46     | 0.58   |
| K   | 0.102     | 0.114 | 2.60     | 2.89   |
| L   | 0.090 BSC |       | 2.29 BSC |        |
| R   | 0.175     | 0.215 | 4.45     | 5.46   |
| S   | 0.020     | 0.050 | 0.51     | 1.27   |
| U   | 0.020     |       | 0.51     |        |
| ٧   | 0.030     | 0.050 | 0.77     | 1.27   |
| Z   | 0.138     |       | 3.51     |        |

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